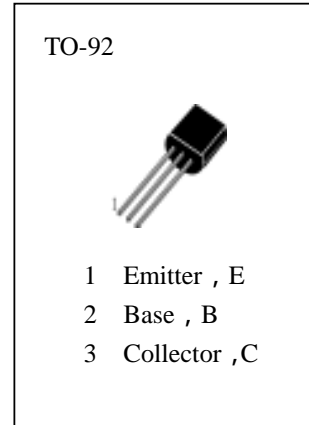




**HIGH VOLTAGE TRANSISTOR**

**ABSOLUTE MAXIMUM RATINGS (  $T_a=25$  )**

- $T_{stg}$ —Storage Temperature..... -55~150
- $T_j$ —Junction Temperature.....150
- $P_C$ —Collector Dissipation.....625mW
- $V_{CBO}$ —Collector-Base Voltage.....500V
- $V_{CEO}$ —Collector-Emitter Voltage.....400V
- $V_{EBO}$ —Emitter-Base Voltage.....6V
- $I_C$ —Collector Current.....300mA



**ELECTRICAL CHARACTERISTICS (  $T_a=25$  )**

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
$BV_{CBO}$	Collector-Base Breakdown Voltage	500			V	$I_C=100 \mu A, I_E=0$
$BV_{CEO}$	Collector-Emitter Breakdown Voltage	400			V	$I_C=1mA, I_B=0$
$BV_{EBO}$	Emitter-Base Breakdown Voltage	6			V	$I_E=100 \mu A, I_C=0$
$I_{CBO}$	Collector Cut-off Current			100	nA	$V_{CB}=400V, I_E=0$
$I_{EBO}$	Emitter-Base Cut-off Current			100	nA	$V_{EB}=4V, I_C=0$
$I_{CES}$	Collector Cut-off Current			500	nA	$V_{CE}=-400V, V_{BE}=0$
$H_{FE} ( 1 )$	DC Current Gain	40				$V_{CE}=10V, I_C=1mA$
$H_{FE} ( 2 )$		60		300		$V_{CE}=10V, I_C=10mA$
$H_{FE} ( 3 )$		45				$V_{CE}=10V, I_C=50mA$
$H_{FE} ( 4 )$		40				$V_{CE}=10V, I_C=100mA$
$V_{CE(sat1)}$	Collector- Emitter Saturation Voltage			0.4	V	$I_C=1mA, I_B=0.1mA$
$V_{CE(sat2)}$				0.5	V	$I_C=10mA, I_B=1mA$
$V_{CE(sat3)}$				0.75	V	$I_C=50mA, I_B=5mA$
$V_{BE(sat)}$	Base-Emitter Saturation Voltage			0.75	V	$I_C=10mA, I_B=1mA$
Cob	Output Capacitance	7			pF	$V_{CB}=20V, I_E=0, F=1MHz$